Tim D Veal

List of Publications by Year
in descending order

167 papers	7,587 citations	36203 51 h-index	60497 81 g-index
170 all docs	170 docs citations	170 times ranked	6862 citing authors

#	Article	IF	Citations
1	Intrinsic Electron Accumulation at Clean InN Surfaces. Physical Review Letters, 2004, 92, 036804.	2.9	453
2	Band gap, electronic structure, and surface electron accumulation of cubic and rhombohedral<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub Physical Review B, 2009, 79, .	1.1	369
3	Electronic and optical properties of single crystal SnS₂: an earth-abundant disulfide photocatalyst. Journal of Materials Chemistry A, 2016, 4, 1312-1318.	5.2	246
4	Surface Electron Accumulation and the Charge Neutrality Level in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>In</mml:mi><mml:mn>2</mml:mn></mml:msub><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2008, 101, 116808.	2.9	236
5	Origin of electron accumulation at wurtzite InN surfaces. Physical Review B, 2004, 69, .	1.1	205
6	Conductivity in transparent oxide semiconductors. Journal of Physics Condensed Matter, 2011, 23, 334214.	0.7	179
7	Band Alignments, Valence Bands, and Core Levels in the Tin Sulfides SnS, SnS₂, and Sn₂S₃: Experiment and Theory. Chemistry of Materials, 2016, 28, 3718-3726.	3.2	172
8	Bandgap and effective mass of epitaxial cadmium oxide. Applied Physics Letters, 2008, 92, .	1.5	158
9	Origin of the n-type conductivity of InN: The role of positively charged dislocations. Applied Physics Letters, 2006, 88, 252109.	1.5	138
10	Shallow donor state of hydrogen in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>In</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:msub xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>SnO</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:ms Implications for conductivi. Physical Review B, 2009, 80, .	1.1	135
11	Valence-band electronic structure of CdO, ZnO, and MgO from x-ray photoemission spectroscopy and quasi-particle-corrected density-functional theory calculations. Physical Review B, 2009, 79, .	1.1	124
12	InN/GaN valence band offset: High-resolution x-ray photoemission spectroscopy measurements. Physical Review B, 2008, 78, .	1.1	122
13	Growth, disorder, and physical properties of ZnSnN2. Applied Physics Letters, 2013, 103, .	1.5	111
14	Determination of the branch-point energy of InN: Chemical trends in common-cation and common-anion semiconductors. Physical Review B, 2008, 77, .	1.1	106
15	Bulk transport measurements in ZnO: The effect of surface electron layers. Physical Review B, 2010, 81, .	1.1	104
16	Quantized Electron Accumulation States in Indium Nitride Studied by Angle-Resolved Photoemission Spectroscopy. Physical Review Letters, 2006, 97, 237601.	2.9	103
17	Universality of electron accumulation at wurtzite c- and a-plane and zinc-blende InN surfaces. Applied Physics Letters, 2007, 91, 092101.	1.5	102
18	Band Gap Dependence on Cation Disorder in ZnSnN₂ Solar Absorber. Advanced Energy Materials, 2015, 5, 1501462.	10.2	96

#	Article	IF	Citations
19	Valence band offset of InNâˆ•AlN heterojunctions measured by x-ray photoelectron spectroscopy. Applied Physics Letters, 2007, 90, 132105.	1.5	89
20	Surface Band-Gap Narrowing in Quantized Electron Accumulation Layers. Physical Review Letters, 2010, 104, 256803.	2.9	86
21	Transition from electron accumulation to depletion at InGaN surfaces. Applied Physics Letters, 2006, 89, 202110.	1.5	85
22	Selfâ€Compensation in Transparent Conducting Fâ€Doped SnO₂. Advanced Functional Materials, 2018, 28, 1701900.	7.8	85
23	Growth and properties of GaSbBi alloys. Applied Physics Letters, 2013, 103, 142106.	1.5	84
24	Isotype Heterojunction Solar Cells Using n-Type Sb₂Se₃ Thin Films. Chemistry of Materials, 2020, 32, 2621-2630.	3.2	83
25	Valence band offset of the ZnO/AlN heterojunction determined by x-ray photoemission spectroscopy. Applied Physics Letters, 2008, 93, .	1.5	78
26	Unification of the electrical behavior of defects, impurities, and surface states in semiconductors: Virtual gap states in CdO. Physical Review B, 2009, 79, .	1.1	76
27	Observation of quantized subband states and evidence for surface electron accumulation in CdO from angle-resolved photoemission spectroscopy. Physical Review B, 2008, 78, .	1.1	75
28	Nonparabolic coupled Poisson-SchrÃ¶dinger solutions for quantized electron accumulation layers: Band bending, charge profile, and subbands at InN surfaces. Physical Review B, 2008, 77, .	1.1	75
29	Origin of High Mobility in Molybdenum-Doped Indium Oxide. Chemistry of Materials, 2015, 27, 2788-2796.	3.2	71
30	High Bi content GaSbBi alloys. Journal of Applied Physics, 2014, 116, .	1.1	70
31	Band gap temperature-dependence of close-space sublimation grown Sb2Se3 by photo-reflectance. APL Materials, 2018, 6, 084901.	2.2	70
32	Observation of shallow-donor muonium in Ga2O3: Evidence for hydrogen-induced conductivity. Applied Physics Letters, 2010, 96, .	1.5	68
33	Temperature dependence of the direct bandgap and transport properties of CdO. Applied Physics Letters, 2013, 102, .	1.5	68
34	In adlayers on<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>c</mml:mi></mml:math>-plane InN surfaces: A polarity-dependent study by x-ray photoemission spectroscopy. Physical Review B, 2007, 76, .	1.1	67
35	Core Levels, Band Alignments, and Valence-Band States in CuSbS₂ for Solar Cell Applications. ACS Applied Materials & Interfaces, 2017, 9, 41916-41926.	4.0	67
36	Electron depletion at InAs free surfaces: Doping-induced acceptorlike gap states. Physical Review B, 2006, 73, .	1.1	65

#	Article	IF	Citations
37	Polarity effects in the x-ray photoemission of ZnO and other wurtzite semiconductors. Applied Physics Letters, 2011, 98, .	1.5	64
38	Resonant doping for high mobility transparent conductors: the case of Mo-doped In₂O₃. Materials Horizons, 2020, 7, 236-243.	6.4	64
39	Valence-band density of states and surface electron accumulation in epitaxial<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>SnO</mml:mi><mml:mn>2</mml:mn></mml:msub></m Physical Review B, 2014, 90, .	1.1	62
40	Transition from electron accumulation to depletion at Î²-Ga2O3 surfaces: The role of hydrogen and the charge neutrality level. APL Materials, 2019, 7, .	2.2	62
41	Identifying Raman modes of Sb₂Se₃ and their symmetries using angle-resolved polarised Raman spectra. Journal of Materials Chemistry A, 2020, 8, 8337-8344.	5.2	62
42	Direct Measurements of Fermi Level Pinning at the Surface of Intrinsically n-Type InGaAs Nanowires. Nano Letters, 2016, 16, 5135-5142.	4.5	60
43	Negative Band Gaps in DiluteInNxSb1â^'xAlloys. Physical Review Letters, 2004, 92, 136801.	2.9	58
44	Valence-band structure of InN from x-ray photoemission spectroscopy. Physical Review B, 2005, 72, .	1.1	57
45	Band anticrossing in GaNxSb1â^'x. Applied Physics Letters, 2006, 89, 111921.	1.5	55
46	Variation of band bending at the surface of Mg-doped InGaN: Evidence ofp-type conductivity across the composition range. Physical Review B, 2007, 75, .	1.1	55
47	Sb-Induced Phase Control of InAsSb Nanowires Grown by Molecular Beam Epitaxy. Nano Letters, 2015, 15, 1109-1116.	4.5	55
48	Surface Structure and Electronic Properties of In₂O₃(111) Single-Crystal Thin Films Grown on Y-Stabilized ZrO₂(111). Chemistry of Materials, 2009, 21, 4353-4355.	3.2	54
49	Surfactant effect of antimony addition to the morphology of self-catalyzed InAs1â^'x Sb x nanowires. Nano Research, 2015, 8, 1309-1319.	5.8	54
50	Photoluminescence spectroscopy of bandgap reduction in dilute InNAs alloys. Applied Physics Letters, 2005, 87, 182114.	1.5	52
51	Electron mobility in CdO films. Journal of Applied Physics, 2011, 109, .	1.1	51
52	Theoretical and experimental studies of electronic band structure for GaSb1â^'xBix in the dilute Bi regime. Journal Physics D: Applied Physics, 2014, 47, 355107.	1.3	50
53	Resonant Ta Doping for Enhanced Mobility in Transparent Conducting SnO₂. Chemistry of Materials, 2020, 32, 1964-1973.	3.2	50
54	Indium Gallium Oxide Alloys: Electronic Structure, Optical Gap, Surface Space Charge, and Chemical Trends within Common-Cation Semiconductors. ACS Applied Materials & Interfaces, 2021, 13, 2807-2819.	4.0	50

#	Article	IF	Citations
55	Band gap reduction in GaNSb alloys due to the anion mismatch. Applied Physics Letters, 2005, 87, 132101.	1.5	49
56	Clean wurtzite InN surfaces prepared with atomic hydrogen. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2005, 23, 617-620.	0.9	48
57	Bi-induced band gap reduction in epitaxial InSbBi alloys. Applied Physics Letters, 2014, 105, .	1.5	48
58	GeSe: Optical Spectroscopy and Theoretical Study of a van der Waals Solar Absorber. Chemistry of Materials, 2020, 32, 3245-3253.	3.2	48
59	Ge interface engineering using ultra-thin La2O3 and Y2O3 films: A study into the effect of deposition temperature. Journal of Applied Physics, 2014, 115, .	1.1	47
60	Temperature dependence of the band gap of GaSb1â^'xBix alloys with 0â€‰<â€‰xâ€‰â‰â€‰0.042 determined by photoreflectance. Applied Physics Letters, 2013, 103, .	1.5	46
61	Thickness dependence of the strain, band gap and transport properties of epitaxial In₂O₃thin films grown on Y-stabilised ZrO₂(111). Journal of Physics Condensed Matter, 2011, 23, 334211.	0.7	45
62	The influence of Sn doping on the growth of In2O3 on Y-stabilized ZrO2(100) by oxygen plasma assisted molecular beam epitaxy. Journal of Applied Physics, 2009, 106, .	1.1	41
63	Vacancy-Ordered Double Perovskite Cs₂TeI₆ Thin Films for Optoelectronics. Chemistry of Materials, 2020, 32, 6676-6684.	3.2	41
64	Indium nitride: Evidence of electron accumulation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2175.	1.6	40
65	Natural Band Alignments and Band Offsets of Sb₂Se₃ Solar Cells. ACS Applied Energy Materials, 2020, 3, 11617-11626.	2.5	40
66	Temperature invariance ofInNelectron accumulation. Physical Review B, 2004, 70, .	1.1	39
67	Valence band density of states of zinc-blende and wurtzite InN from x-ray photoemission spectroscopy and first-principles calculations. Physical Review B, 2008, 77, .	1.1	39
68	Inversion and accumulation layers at InN surfaces. Journal of Crystal Growth, 2006, 288, 268-272.	0.7	37
69	Realization of Vertically Aligned, Ultrahigh Aspect Ratio InAsSb Nanowires on Graphite. Nano Letters, 2015, 15, 4348-4355.	4.5	37
70	Band Alignments, Band Gap, Core Levels, and Valence Band States in Cu₃BiS₃ for Photovoltaics. ACS Applied Materials & Interfaces, 2019, 11, 27033-27047.	4.0	37
71	Unintentional conductivity of indium nitride: transport modelling and microscopic origins. Journal of Physics Condensed Matter, 2009, 21, 174201.	0.7	36
72	Contactless electroreflectance and theoretical studies of band gap and spin-orbit splitting in InP_{1â^'x}Bi_x dilute bismide with xâ€‰â‰â€‰0.034. Applied Physics Letters, 2014, 105, 222104.	1.5	36

#	Article	IF	Citations
73	Valence band modification of Cr₂O₃by Ni-doping: creating a high figure of merit p-type TCO. Journal of Materials Chemistry C, 2017, 5, 12610-12618.	2.7	36
74	Photoluminescence of InNAs alloys: S-shaped temperature dependence and conduction-band nonparabolicity. Physical Review B, 2007, 76, .	1.1	35
75	Atypically small temperature-dependence of the direct band gap in the metastable semiconductor copper nitride<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Cu</mml:mi><mml:mn>3</mml:mn></m mathvariant="normal">N</mml:mi></mml:mrow></mml:math>. Physical Review B, 2017, 95, .	1.1	35
76	Influence of Polymorphism on the Electronic Structure of Ga₂O₃. Chemistry of Materials, 2020, 32, 8460-8470.	3.2	35
77	Band bending at the surfaces of In-rich InGaN alloys. Journal of Applied Physics, 2008, 104, .	1.1	33
78	Growth of dilute GaNSb by plasma-assisted MBE. Journal of Crystal Growth, 2005, 278, 188-192.	0.7	31
79	Core-level photoemission spectroscopy of nitrogen bonding in GaNxAs1âˆ’x alloys. Applied Physics Letters, 2004, 85, 1550-1552.	1.5	30
80	The influence of conduction band plasmons on core-level photoemission spectra of InN. Surface Science, 2008, 602, 871-875.	0.8	30
81	Surface, bulk, and interface electronic properties of nonpolar InN. Applied Physics Letters, 2010, 97, .	1.5	30
82	Low- and high-energy photoluminescence from GaSb_{1âˆ’}<i>_x</i>Bi<i>_x</i>with 0 <<i>x</i>â‰ 0.042. Applied Physics Express, 2014, 7, 111202.	1.1	30
83	Profiling of electron accumulation layers in the near-surface region of InAs (110). Physical Review B, 2001, 64, .	1.1	29
84	How Oxygen Exposure Improves the Back Contact and Performance of Antimony Selenide Solar Cells. ACS Applied Materials & Interfaces, 2020, 12, 52595-52602.	4.0	29
85	Passivation and reconstruction-dependent electron accumulation at sulphur treated InAs() surfaces. Surface Science, 2003, 523, 179-188.	0.8	28
86	Growth of ZnSnN2 by Molecular Beam Epitaxy. Journal of Electronic Materials, 2014, 43, 884-888.	1.0	28
87	Bi flux-dependent MBE growth of GaSbBi alloys. Journal of Crystal Growth, 2015, 425, 241-244.	0.7	27
88	Ab-Initio Studies of Electronic and Spectroscopic Properties of MgO, ZnO and CdO. Journal of the Korean Physical Society, 2008, 53, 2811-2815.	0.3	26
89	Optical absorption by dilute GaNSb alloys: Influence of N pair states. Applied Physics Letters, 2013, 103, 042110.	1.5	22
90	Sulphur-induced electron accumulation on InAs: a comparison of the (001) and (111)B surfaces. Surface Science, 2003, 544, 320-328.	0.8	21

#	ARTICLE	IF	CITATIONS
91	HREELS and photoemission study of GaSb()-(1Ã—3) surfaces prepared by optimal atomic hydrogen cleaning. Surface Science, 2002, 499, 251-260.	0.8	20
92	X-ray photoemission studies of the electronic structure of single-crystalline CdO(100). Superlattices and Microstructures, 2007, 42, 197-200.	1.4	20
93	Giant Reduction of InN Surface Electron Accumulation: Compensation of Surface Donors by Mg Dopants. Physical Review Letters, 2012, 109, 247605.	2.9	20
94	The first 25 years of semiconductor muonics at ISIS, modelling the electrical activity of hydrogen in inorganic semiconductors and high-<i>Îº</i>dielectrics. Physica Scripta, 2013, 88, 068503.	1.2	20
95	Effect of hydrogen in dilute InNxSb1â^'x alloys grown by molecular beam epitaxy. Applied Physics Letters, 2003, 83, 1776-1778.	1.5	19
96	X-ray photoemission spectroscopy determination of the InN/yttria stabilized cubic-zirconia valence band offset. Applied Physics Letters, 2007, 91, 112103.	1.5	19
97	N incorporation in GaInNSb alloys and lattice matching to GaSb. Journal of Applied Physics, 2013, 113, 033502.	1.1	19
98	Sb 5s² lone pairs and band alignment of Sb₂Se₃: a photoemission and density functional theory study. Journal of Materials Chemistry C, 2020, 8, 12615-12622.	2.7	19
99	Controlled oxide removal for the preparation of damage-free InAs(110) surfaces. Applied Physics Letters, 2000, 77, 1665-1667.	1.5	18
100	Electron accumulation at InN/AlN and InN/GaN interfaces. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2246-2249.	0.8	18
101	Surface electronic properties of clean and S-terminated InSb(001) and (111)B. Journal of Applied Physics, 2008, 104, 083709.	1.1	18
102	Optimization of self-catalyzed InAs Nanowires on flexible graphite for photovoltaic infrared photodetectors. Scientific Reports, 2017, 7, 46110.	1.6	18
103	Evidence of a second-order Peierls-driven metal-insulator transition in crystalline NbO2. Physical Review Materials, 2019, 3, .	0.9	18
104	Scanning tunnelling spectroscopy of quantized electron accumulation at InxGa1â^'xN surfaces. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 85-92.	0.8	17
105	Surface electronic properties of undoped InAlN alloys. Applied Physics Letters, 2008, 92, 172105.	1.5	17
106	Controlled nitrogen incorporation in GaNSb alloys. AIP Advances, 2011, 1, .	0.6	17
107	Chemical etching of Sb₂Se₃ solar cells: surface chemistry and back contact behaviour. JPhys Energy, 2019, 1, 045001.	2.3	17
108	Surface electronic properties of nâ€•and pâ€•type InGaN alloys. Physica Status Solidi (B): Basic Research, 2008, 245, 881-883.	0.7	16

#	Article	IF	Citations
109	Intrinsic point defects and the n - and p -type dopability of the narrow gap semiconductors GaSb and InSb. Physical Review B, 2019, 100, .	1.1	16
110	Influence of growth conditions and polarity on interface-related electron density in InN. Journal of Applied Physics, 2008, 104, .	1.1	15
111	Sulfur passivation of InN surface electron accumulation. Applied Physics Letters, 2009, 95, .	1.5	15
112	Ge 4s² lone pairs and band alignments in GeS and GeSe for photovoltaics. Journal of Materials Chemistry A, 2021, 9, 22440-22452.	5.2	15
113	Band alignment of Sb2O3 and Sb2Se3. Journal of Applied Physics, 2021, 129, .	1.1	15
114	Dilute antimonide nitrides for very long wavelength infrared applications. , 2006, 6206, 201.		14
115	Growth and characterisation of high quality MBE grown InNxSb1â€“x. Physica Status Solidi - Rapid Research Letters, 2007, 1, 104-106.	1.2	14
116	Influence of charged-dislocation density variations on carrier mobility in heteroepitaxial semiconductors: The case of SnO<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>on sapphire. Physical Review B, 2012, 86, .	1.1	14
117	N incorporation and associated localized vibrational modes in GaSb. Physical Review B, 2014, 89, .	1.1	14
118	Band gap temperature-dependence and exciton-like state in copper antimony sulphide, CuSbS2. APL Materials, 2018, 6, .	2.2	14
119	In-adlayers on non-polar and polar InN surfaces: Ion scattering and photoemission studies. Physica B: Condensed Matter, 2007, 401-402, 351-354.	1.3	13
120	ZnSnN2: A new earth-abundant element semiconductor for solar cells. , 2012, , .		13
121	Low-energy nitrogen ion implantation of InSb. Journal of Applied Physics, 2004, 96, 4935-4938.	1.1	12
122	Hole density and acceptor-type defects in MBE-grown GaSb_{1-<i>x</i>}â€‰Bi_{<i>x</i>}. Journal Physics D: Applied Physics, 2017, 50, 295102.	1.3	12
123	Photoelectron spectroscopy study of Ga1âˆ'xMnxAs(001) surface oxide and low temperature cleaning. Surface Science, 2005, 585, 66-74.	0.8	11
124	Inâ€vacancies in Siâ€doped InN. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1083-1086.	0.8	11
125	Self-compensation in highly n-type InN. Applied Physics Letters, 2012, 101, 011903.	1.5	11
126	Photoreflectance spectroscopy of GaInSbBi and AlGaSbBi quaternary alloys. Applied Physics Letters, 2014, 105, .	1.5	11

#	Article	IF	Citations
127	Graphitic platform for self-catalysed InAs nanowires growth by molecular beam epitaxy. Nanoscale Research Letters, 2014, 9, 321.	3.1	11
128	Na2Fe2OS2, a new earth abundant oxysulphide cathode material for Na-ion batteries. Journal of Materials Chemistry A, 2020, 8, 20553-20569.	5.2	11
129	Sn 5s2 lone pairs and the electronic structure of tin sulphides: A photoreflectance, high-energy photoemission, and theoretical investigation. Physical Review Materials, 2020, 4, .	0.9	11
130	Molecular-beam epitaxy and lattice parameter of GaN_{<i>x</i>}Sb_{1âˆ’<i>x</i>}: deviation from Vegard's law for<i>x</i>> 0.02. Journal Physics D: Applied Physics, 2013, 46, 264003.	1.3	10
131	Extreme band bending at MBE-grown InAs(001) surfaces induced by in situ sulphur passivation. Journal of Crystal Growth, 2002, 237-239, 196-200.	0.7	9
132	Electron spectroscopy of dilute nitrides. Journal of Physics Condensed Matter, 2004, 16, S3201-S3214.	0.7	9
133	Band gap reduction in InN<i>x</i>Sb1-<i>x</i> alloys: Optical absorption, k Â· P modeling, and density functional theory. Applied Physics Letters, 2016, 109, .	1.5	9
134	Growth of dilute nitride alloys of GaInSb lattice-matched to GaSb. Journal of Crystal Growth, 2007, 304, 338-341.	0.7	8
135	Increased <i>p</i>-type conductivity in GaN<i>x</i>Sb1âˆ’<i>x</i>, experimental and theoretical aspects. Journal of Applied Physics, 2015, 118, .	1.1	8
136	Indium-incorporation enhancement of photoluminescence properties of Ga(In)SbBi alloys. Journal Physics D: Applied Physics, 2017, 50, 375102.	1.3	8
137	Electron dynamics in InNxSb1âˆ’x. Applied Physics Letters, 2003, 83, 2169-2171.	1.5	7
138	Growth and Characterization of Sb<inf>2</inf> Se<inf>3</inf> Single Crystals for Fundamental Studies. , 2018, , .		7
139	Growth and characterisation of dilute antimonide nitride materials for long-wavelength applications. Microelectronics Journal, 2009, 40, 399-402.	1.1	6
140	Structural, electrical and optical characterization of MOCVD grown In-rich InGaN layers. Journal of Crystal Growth, 2012, 358, 51-56.	0.7	6
141	GeSe photovoltaics: doping, interfacial layer and devices. Faraday Discussions, 0, 239, 250-262.	1.6	6
142	MBE growth and characterization of Mn-doped InN. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, .	0.6	5
143	Influence of annealing on the electrical characteristic of GaSbBi Schottky diodes. Journal of Applied Physics, 2019, 126, .	1.1	5
144	InN{0001} polarity by ion scattering spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2301-2304.	0.8	4

#	Article	IF	Citations
145	Dielectric function of degenerateInSb: Beyond the hydrodynamic model. Physical Review B, 2006, 73, .	1.1	4
146	InN: Fermi level stabilization by low-energy ion bombardment. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1841-1845.	0.8	4
147	Doping-dependence of subband energies in quantized electron accumulation at InN surfaces. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 536-542.	0.8	4
148	Stable passivation of InN surface electron accumulation with sulphur treatment. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1605-1607.	0.8	4
149	Electronic Properties of Post-transition Metal Oxide Semiconductor Surfaces. Springer Series in Materials Science, 2012, , 127-145.	0.4	4
150	Surface electronic properties of In-rich InGaN alloys grown by MOCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 662-665.	0.8	4
151	Impact of degeneraten-doping on the optical absorption edge in transparent conducting cadmium oxide. , 2013, , .		4
152	Temperature-dependent two-dimensional plasmons at clean and hydrogenated Ge(001) surfaces. Physical Review B, 2000, 62, 7330-7335.	1.1	3
153	Plasmon damping in molecular beam epitaxial-grown InAs(100). Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1766.	1.6	3
154	Determination of the substitutional nitrogen content and the electron effective mass in InNxSb1â^'x (001) epitaxial layers. IEE Proceedings: Optoelectronics, 2003, 150, 102.	0.8	3
155	Sulfur passivation of surface electrons in highly Mg-doped InN. Journal of Applied Physics, 2013, 114, 103702.	1.1	3
156	Response to â€œComment on â€˜Bandgap and effective mass determination of epitaxial cadmium oxideâ€™â€• [Appl. Phys. Lett. 92, 106103 (2008)]. Applied Physics Letters, 2008, 92, 106104.	1.5	2
157	Surface electronic properties of Mgâ€doped InAlN alloys. Physica Status Solidi (B): Basic Research, 2009, 246, 1169-1172.	0.7	2
158	Accelerating the development of new solar absorbers by photoemission characterization coupled with density functional theory. JPhys Energy, 2021, 3, 032001.	2.3	2
159	Long-Life and pH-Stable SnO₂-Coated Au Nanoparticles for SHINERS. Journal of Physical Chemistry C, 0, , .	1.5	2
160	Fuchsâ€“Kliewer phonon excitations in GaNAs alloys. Journal of Applied Physics, 2004, 95, 8466-8468.	1.1	1
161	The donor nature of muonium in undoped, heavily n-type and p-type InAs. Journal of Physics Condensed Matter, 2009, 21, 075803.	0.7	1
162	Epitaxial InGaN on nitridated Si(111) for photovoltaic applications. , 2012, , .		1

#	Article	IF	Citations
163	Transparent Ta doped SnO<inf>2</inf> films deposited by RF co-sputtering. , 2018, , .		1
164	Nitrogen pair-induced temperature insensitivity of the band gap of GaNSb alloys. Journal Physics D: Applied Physics, 2019, 52, 045105.	1.3	0
165	Band offsets of metal oxide contacts on TlBr radiation detectors. Journal of Applied Physics, 2021, 130, 175305.	1.1	0
166	Growth and Characterisation of Dilute Antimonide Nitride Materials for Long Wavelength Applications. Springer Proceedings in Physics, 2008, , 49-51.	0.1	0
167	GaSbBi Metal Semiconductor Metal Detectors for Mid-Infrared Sensing. Frontiers in Electronic Materials, 0, 2, .	1.6	0